

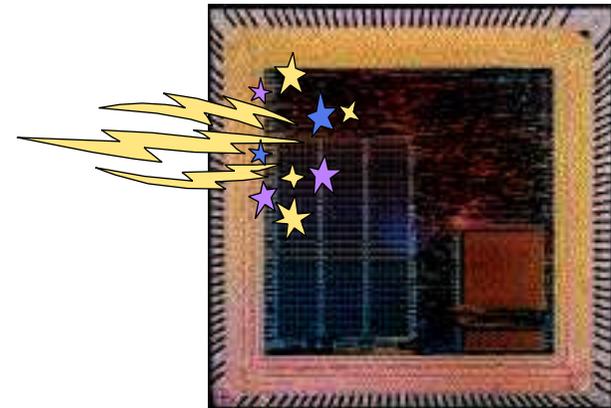


-ray Irradiation Test of AMT-TEG1

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- Introduction
- Radiation Test Results
 - * Ring Oscillator
 - * Transistor parameters
- Summary

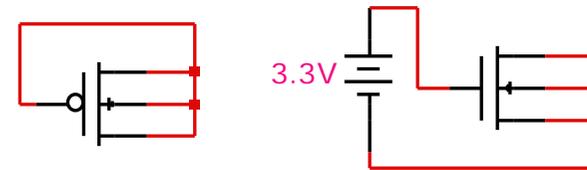


Introduction

- **AMT-TEG1** chip was developed and fabricated last autumn. Main purpose of this chip is evaluating basic TDC elements (PLL, LVDS, JTAG ...).
- Many parts are designed from Verilog source codes which are imported from **AMT-0** (Jorgen's design).
- AMT-TEG1 is processed in a new **0.3 μm CMOS** process (Toshiba TC220G gate array).
- Basic circuit elements were tested successfully.
- The chip contains a **Ring Oscillator** and **NMOS and PMOS transistors** for **radiation test**.

Test Condition

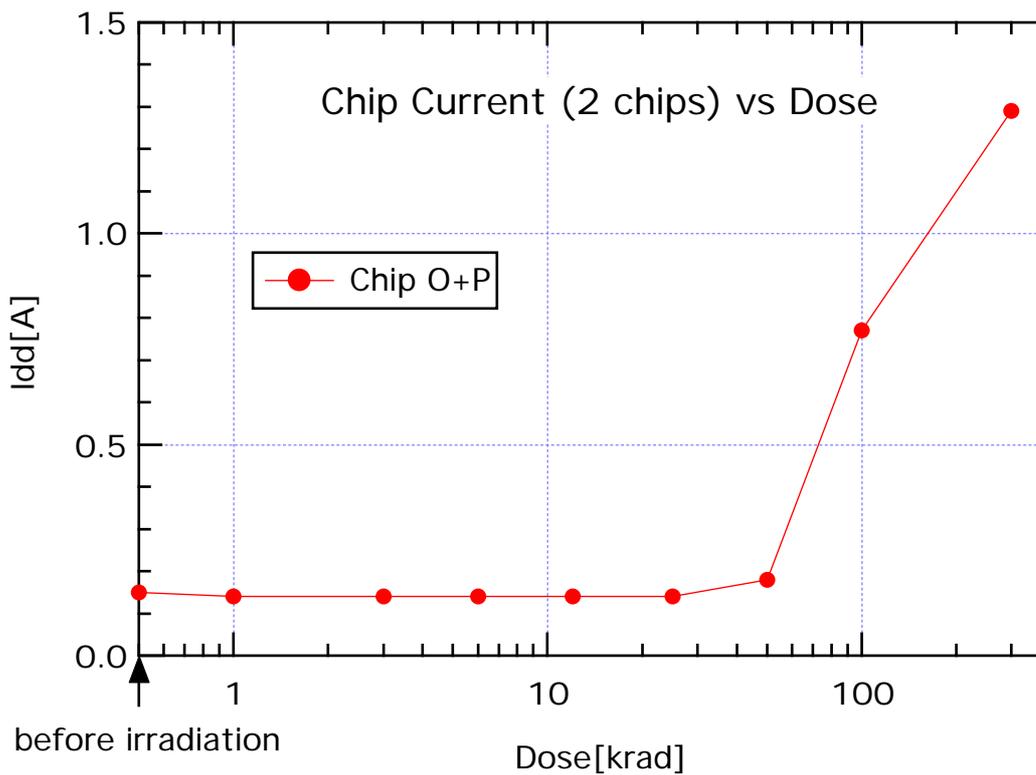
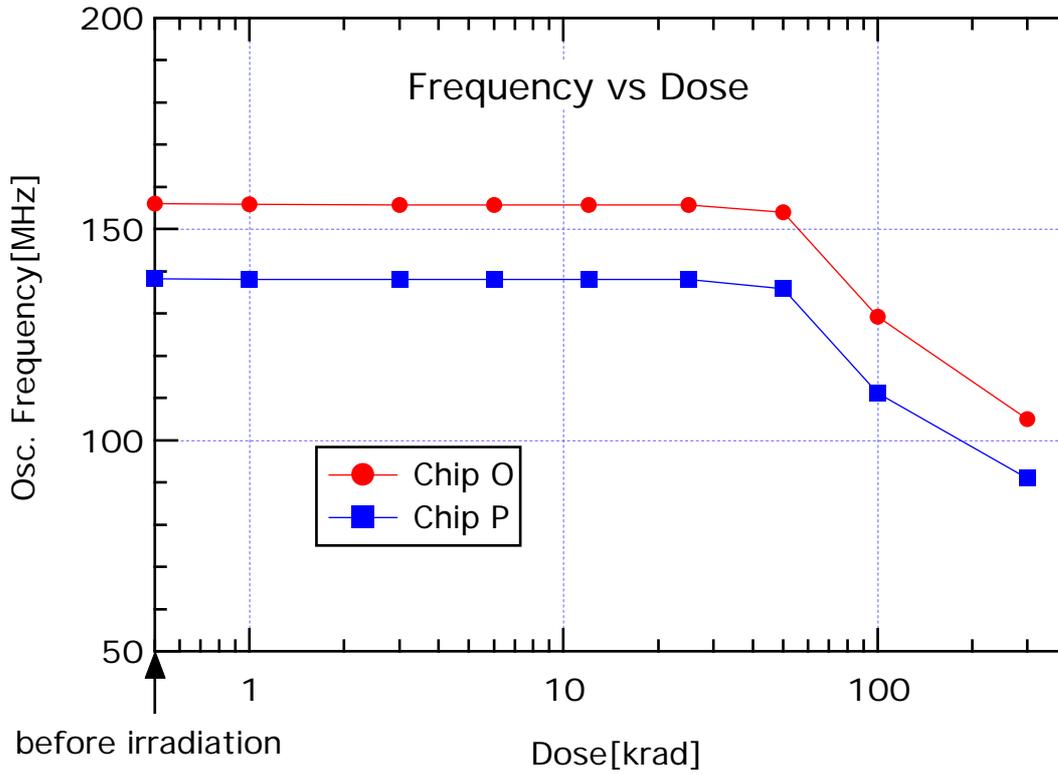
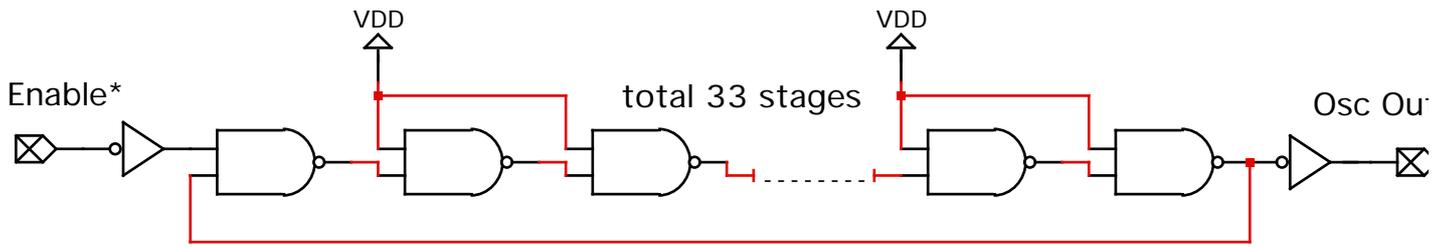
- Irradiated chip : AMT-TEG1(Toshiba 0.3 μm CMOS).
- Source : ^{60}Co (~90 rad(Si)/sec, Total dose ~ 100 krad(Si))
- Follow MIL-STD-883 method 1019.4. After the irradiation, 100 ° C, 1 week annealing was done.
- Transistors were biased in worst condition during irradiation.



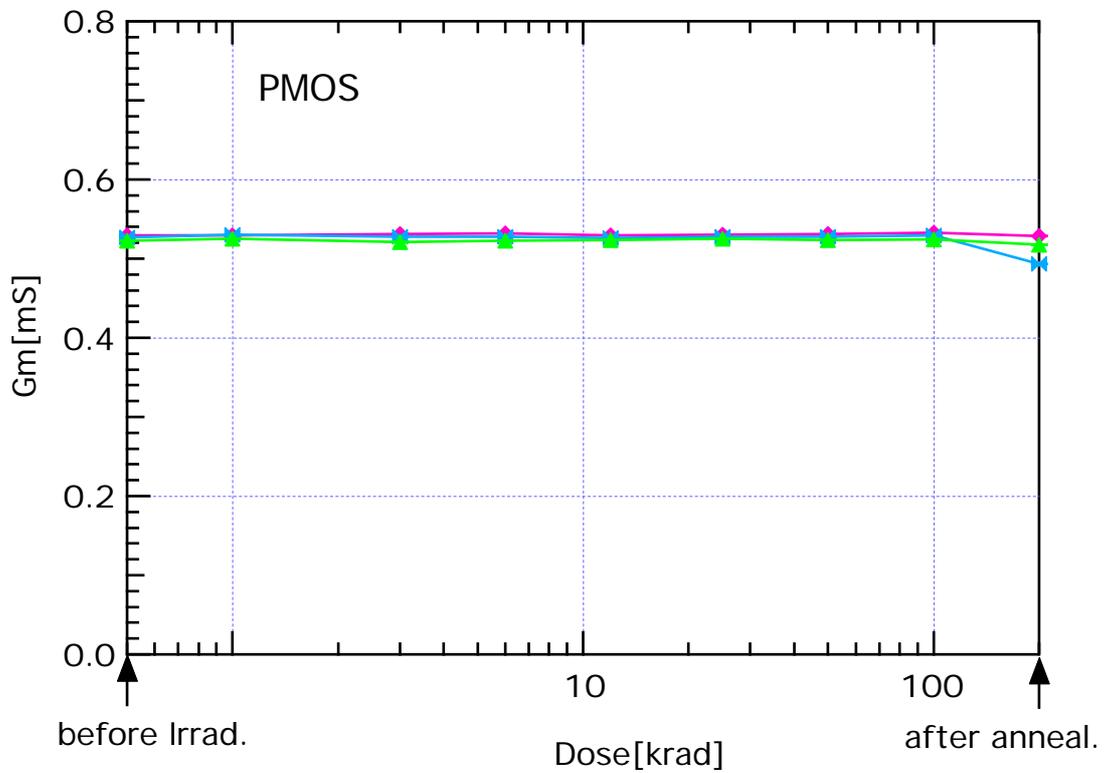
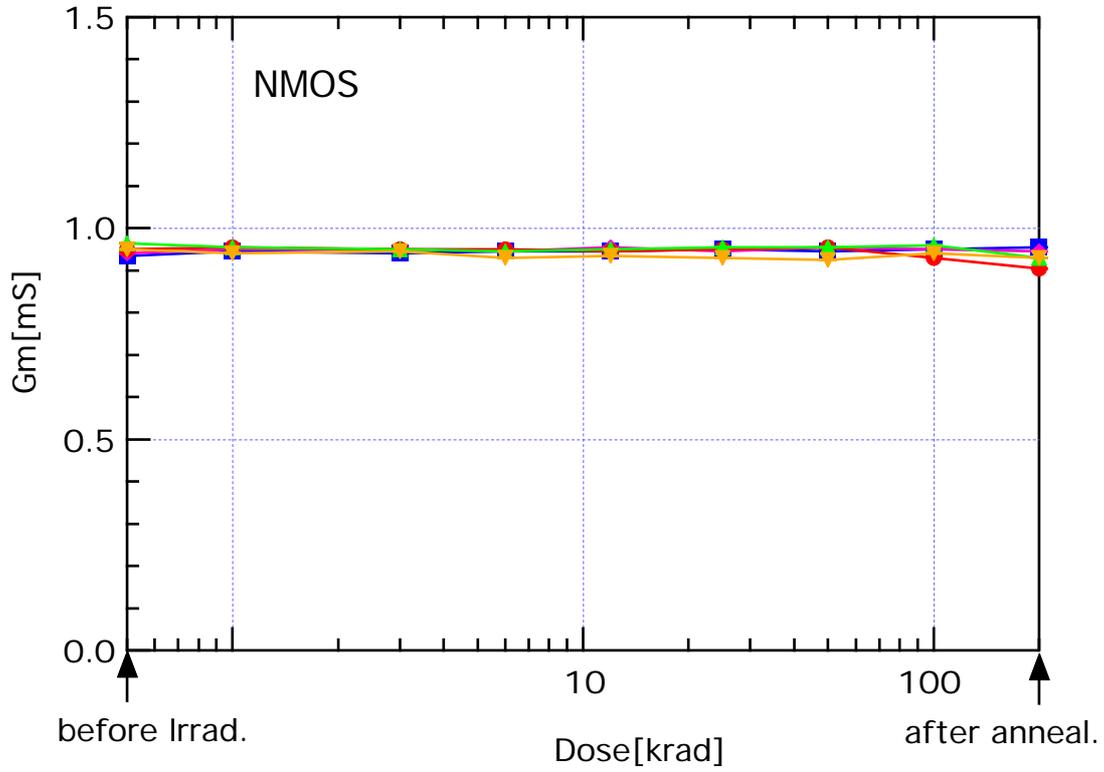
Worst Bias(P short, N On)

- ATLAS requirement : 1.1 krad/year (@MDT Endcap, Safety factor=4).
- Test transistors are directly connected to pins without protection diodes. We handled the chip with the greatest care, but some transistors were broken during the test.

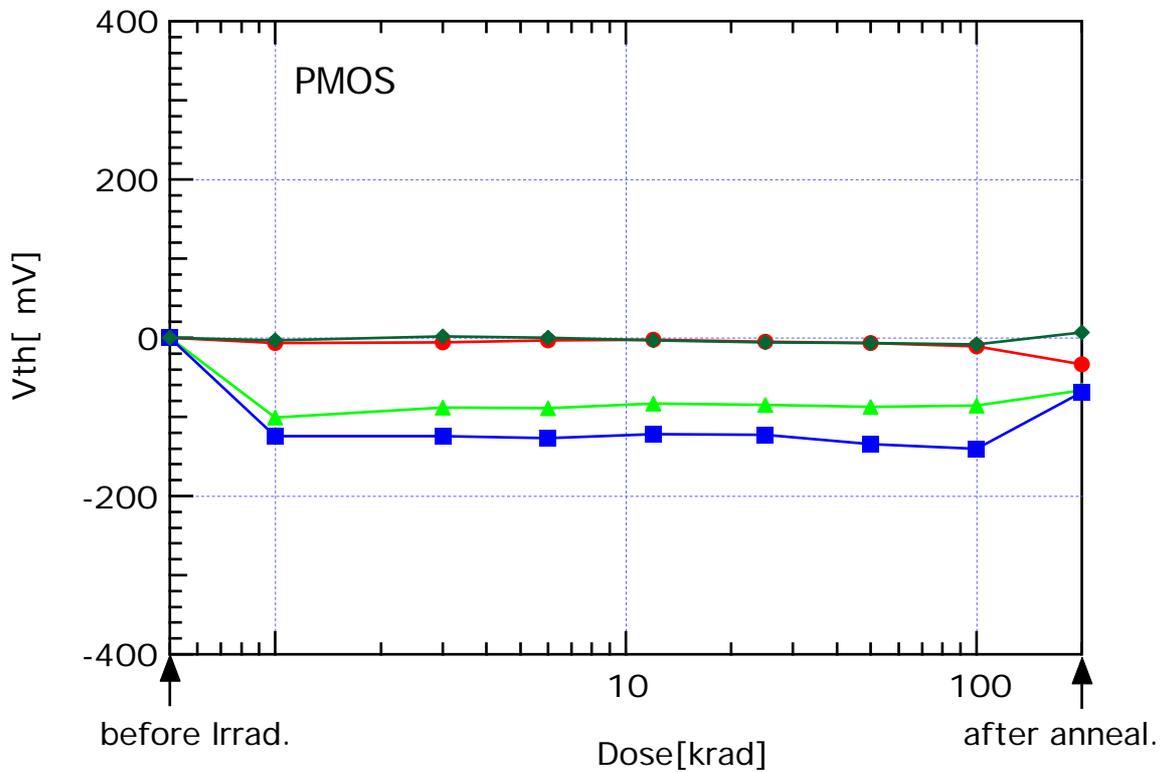
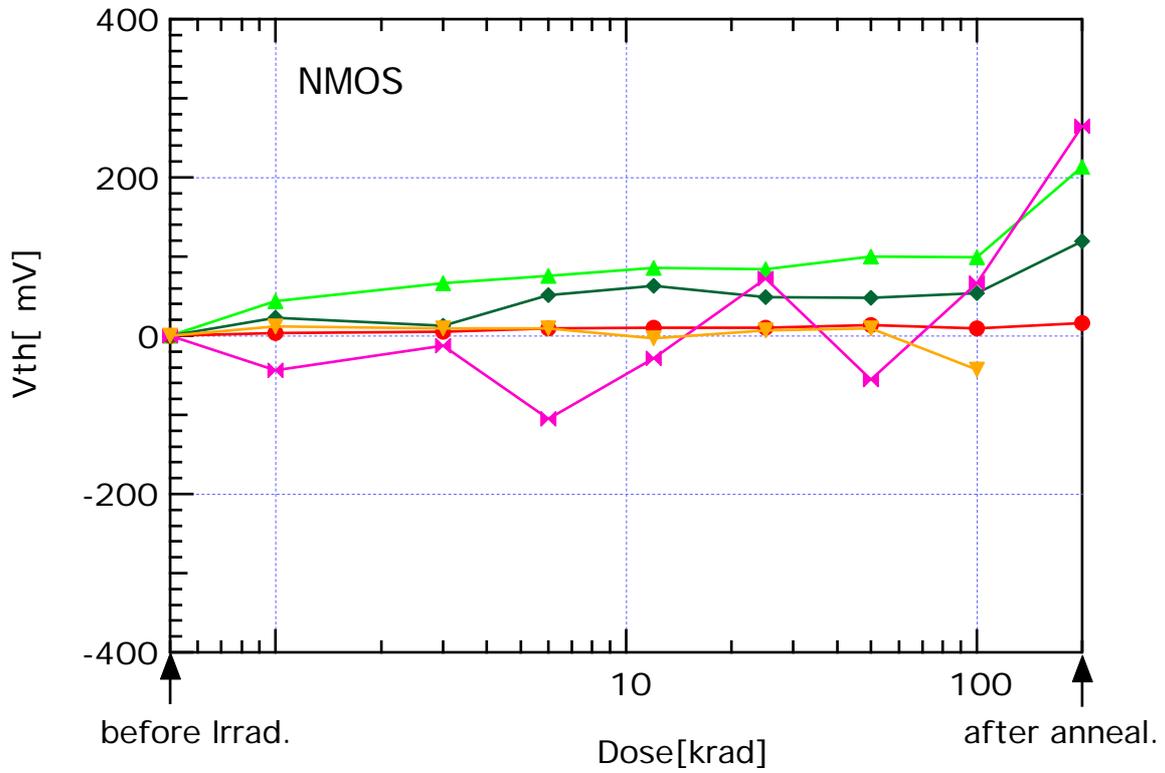
AMT-TEG1 Ring Oscillator



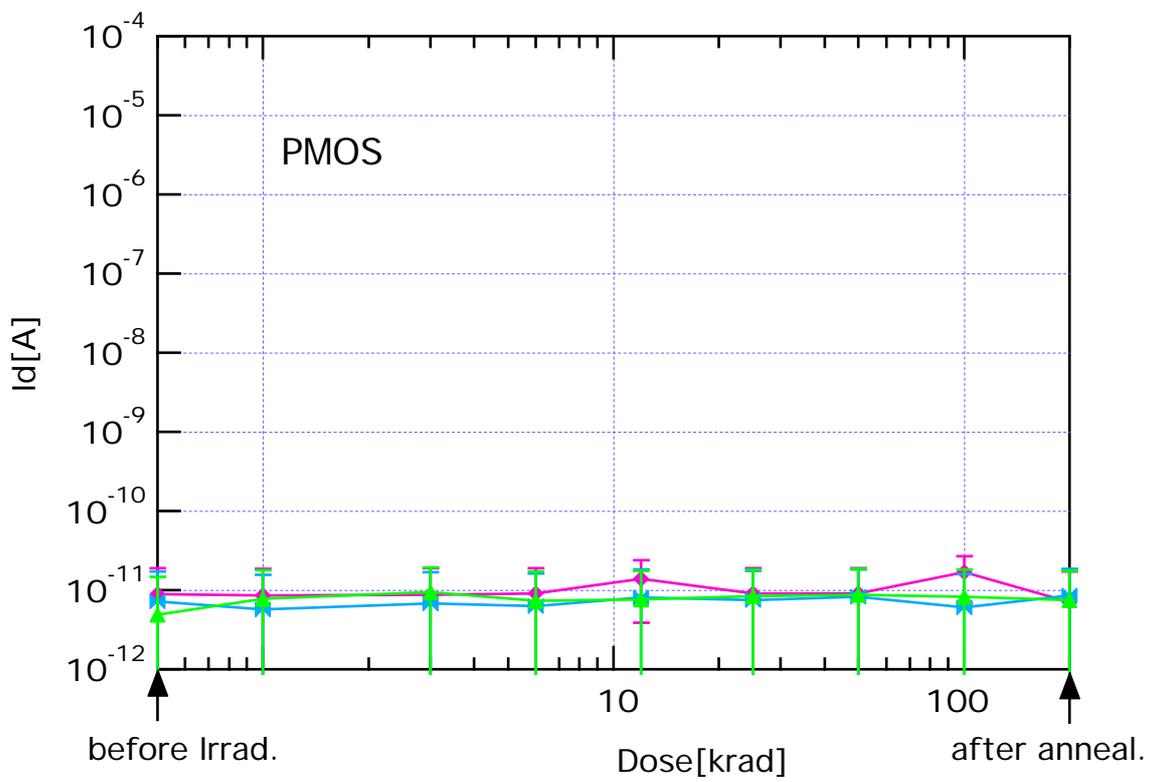
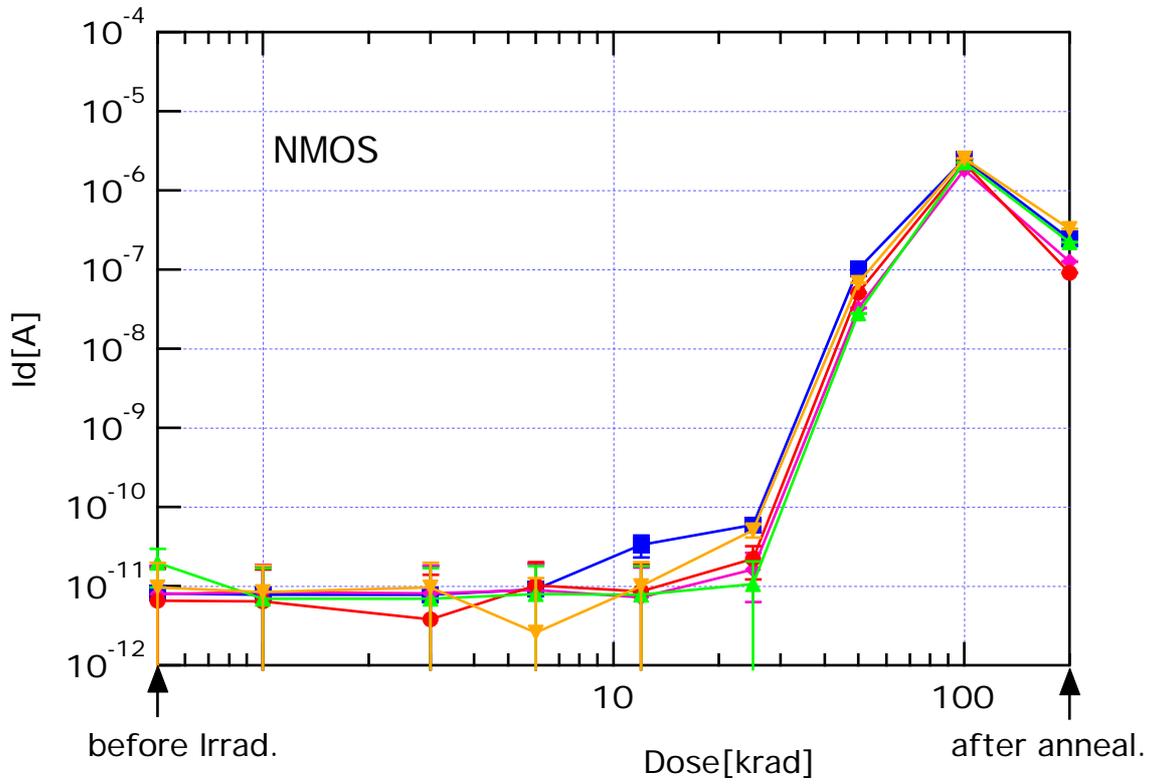
Gm Variation ($V_{ds}=3V$, $V_{gs}=3V$, $V_{sub}=0V$)



Threshold Variation



Drain Leak Current ($V_{ds}=3V$, $V_{gs}=0V$, $V_{sub}=0V$)



Summary

- ❑ Gamma-ray irradiation was done for the AMT-TEG1 (0.3 μ m CMOS).
- ❑ Ring Oscillator shows no performance degradation up to 50 krad.
- ❑ No visible change in G_m up to 100 krad.
- ❑ Threshold shift (V_{th}) is less than 200mV at 100 krad. However, there is no systematic tendency, so this might be caused mainly by ill-handling of the transistor.
- ❑ NMOS drain leak current starts increasing above 25 krad:
 $I_d < 2 \times 10^{-6}$ A @ 100krad. There is no leak current increase in PMOS.
(Current increase for 100 k gates ~ 100 mA @ 100krad)
- ❑ **Conclusion: The 0.3 μ m process has enough γ -radiation tolerance for the ATLAS MDT.**
- ❑ Neutron irradiation test will be scheduled.
- ❑ AMT-TEG2 design will be finished before the summer.